



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

**SURFACE MOUNT
General Purpose PNP Transistor**

VOLTAGE 50 Volts CURRENT 0.15 Ampere

2SA1037MPT

APPLICATION

* Small Power Amplifier .

FEATURE

- * Small surface mounting type. (SOT-723)
- * Low saturation voltage $V_{CE(sat)} = -0.5V(\text{max.})(I_c = -50mA)$
- * Low cob. $C_{ob} = 4.0pF(\text{Typ.})$
- * $P_c = 150mW$ (Collector power dissipation).

CONSTRUCTION

- * PNP Silicon Transistor
- * Epitaxial planner type

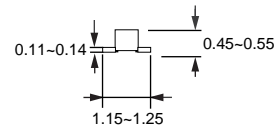
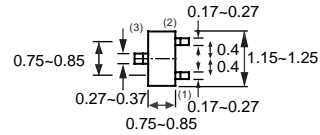
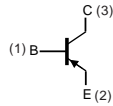
MARKING

- * HFE(Q):38
- * HFE(R):39
- * HFE(S):40



SOT-723

CIRCUIT



Dimensions in millimeters

SOT-723

MAXIMUM RATINGS (At $T_A = 25^\circ C$ unless otherwise noted)

| RATINGS | CONDITION | SYMBOL | MIN. | MAX. | UNITS |
|-----------------------------|-----------------------|-----------|------|------|------------|
| Collector - Base Voltage | Open Emitter | V_{CB0} | - | -60 | Volts |
| Collector - Emitter Voltage | Open Base | V_{CE0} | - | -50 | Volts |
| Emitter - Base Voltage | Open Collector | V_{EB0} | - | -6 | Volts |
| Collector Current DC | | I_c | - | -150 | mAmps |
| Collector Power Dissipation | $T_A \leq 25^\circ C$ | P_{TOT} | - | 150 | mW |
| Storage Temperature | | T_{STG} | -55 | +150 | $^\circ C$ |
| Junction Temperature | | T_J | - | +150 | $^\circ C$ |

Note

1. Transistor mounted on ceramic substrate 50mmX50mmX0.8t.
2. Measured at Pulse Width 300 us, Duty Cycle 2%.

RATING CHARACTERISTICS (2SA1037MPT)

ELECTRICAL CHARACTERISTICS (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

| PARAMETERS | CONDITION | SYMBOL | MIN. | TYPE | MAX. | UNITS |
|--------------------------------------|---|-------------|------|------|------|---------------|
| Collector Cut-off Current | $V_{CB} = -6\text{V}$ | I_{CBO} | - | - | -0.1 | μA |
| Emitter Cut-off Current | $V_{EB} = -6\text{V}$ | I_{EBO} | - | - | -0.1 | μA |
| DC Current Gain | $V_{CE} = -6\text{V}$; Note 1 $I_C = -1\text{mA}$; Note 2 | h_{FE} | 120 | - | 560 | |
| Collector-Emitter Saturation Voltage | $I_C = -50\text{mA}$; $I_B = -5\text{mA}$ | V_{CEsat} | - | - | -0.5 | Volts |
| Collector-Emitter Breakdown Voltage | $I_C = -1\text{mA}$ | V_{CEO} | -50 | - | - | Volts |
| Output Collector Capacitance | $I_E = I_C = 0$; $V_{CE} = -12\text{V}$; $f = 1\text{MHz}$ | C_{ob} | - | 4.0 | 5.0 | pF |
| Transition Frequency | $I_E = 2\text{mA}$; $V_{CE} = -12\text{V}$; $f = 30\text{MHz}$ | f_T | - | 140 | - | MHz |

Note :

1. Pulse test: $t_p \leq 300\mu\text{Sec}$; $\delta \leq 0.02$.
2. h_{FE} : Classification Q: 120 to 270, R: 180 to 390, S: 270 to 560

RATING CHARACTERISTIC CURVES (2SA1037MPT)

Fig.1 Grounded emitter propagation characteristics

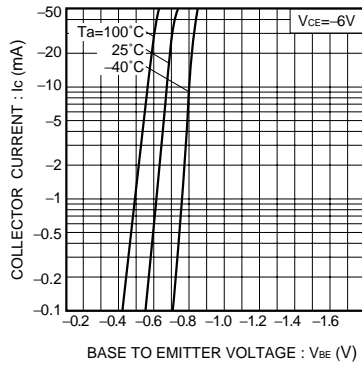


Fig.2 Grounded emitter output characteristics (1)

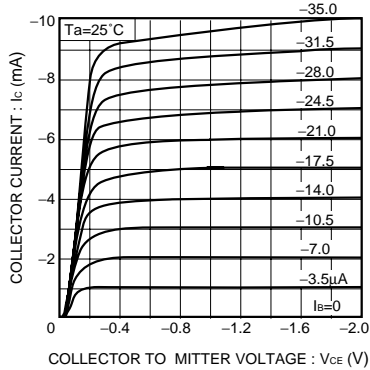
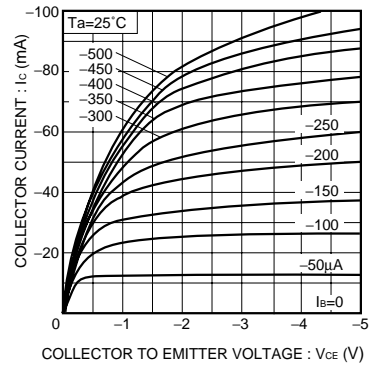


Fig.3 Grounded emitter output characteristics (2)



RATING CHARACTERISTIC CURVES (2SA1037MPT)

Fig.4 Collector-emitter saturation voltage vs. collector current

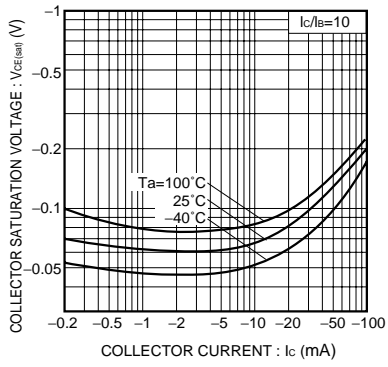


Fig.5 DC current gain vs. collector current

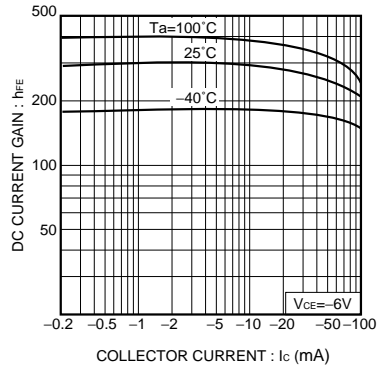


Fig.6 Gain bandwidth product vs. emitter current

